

Title (en)

METHOD FOR FORMING A SEMICONDUCTOR DEVICE HAVING A SALICIDE LAYER

Title (de)

VERFAHREN ZUR BILDUNG EINES HALBLEITERBAUELEMENTS MIT EINER SALIZIDSCHICHT

Title (fr)

PROCEDE DESTINE A PRODUIRE UN DISPOSITIF SEMI-CONDUCTEUR PRESENTANT UNE COUCHE DE SALICIDE

Publication

EP 1955368 A1 20080813 (EN)

Application

EP 05817791 A 20051121

Priority

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Abstract (en)

[origin: WO2007057048A1] A method for forming a semiconductor device and selectively forming a salicide layer is described. In one embodiment, the method includes depositing a metal layer over a semiconductor substrate having a first area (20) and a second area (24), wherein the first area and the second area include silicon, removing the metal layer over the second gate electrode, and reacting the metal layer with the first area to form a salicide layer (48) over the first area. In one embodiment, the first area and the second area include a first gate electrode and a second gate electrode, respectively.

IPC 8 full level

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CPC (source: EP US)

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